MSKSEMI















ESD

TVS

TSS

MOV

GDT

PLED

Broduct data sheet













SOT - 23



- 2. EMITTER
- 3. COLLECTOR

TRANSISTOR (PNP)

FEATURES

High Breakdown Voltage

MARKING:4D

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-400	V
V _{CEO}	Collector-Emitter Voltage	-400	V
V _{EBO}	Emitter-Base Voltage	-5	V
Ic	Collector Current -Continuous	-200	mA
I _{CM}	Collector Current -Pulsed	-300	mA
Pc	Collector Power Dissipation	350	mW
R _{OJA}	Thermal Resistance From Junction To Ambient	357	°C/W
T_J, T_stg	Operation Junction and Storage Temperature Range	-55∼+150	ပူ

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

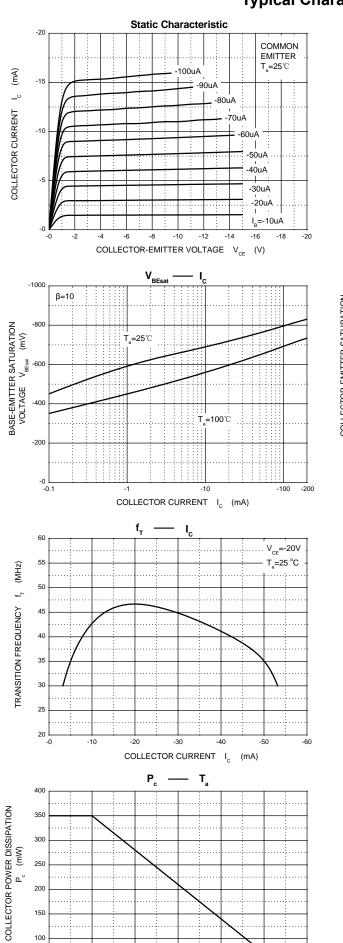
Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA, I _E =0	-400			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-400			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I _E =-100μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-400V, I _E =0			-0.1	μA
Collector cut-off current	I _{CEO}	V _{CE} =-400V, I _B =0			-5	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-4V, I _C =0			-0.1	μA
	h _{FE(1)}	V _{CE} =-10V, I _C =-10mA	80		300	
DC current gain	h _{FE(2)}	V _{CE} =-10V, I _C =-1mA	70			
De current gam	h _{FE(3)}	V _{CE} =-10V, I _C =-100mA	40			
	h _{FE(4)}	V _{CE} =-10V, I _C =-50mA	40			
Collector-emitter saturation voltage	V _{CE(sat)1}	I _C =-10mA, I _B =-1mA			-0.2	V
Conector-enlitter Saturation voltage	V _{CE(sat)2}	I _C =-50mA, I _B =-5mA			-0.3	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-10mA, I _B =-1mA			-0.75	V
Transition fraguency	f⊤	V _{CE} =-20V,I _C =-10mA,	50			MHz
Transition frequency	IŢ	f=30MHz	50			IVII



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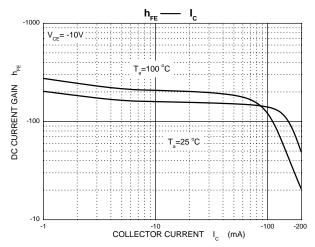
Compiance

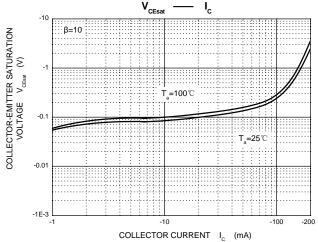
Typical Characteristics

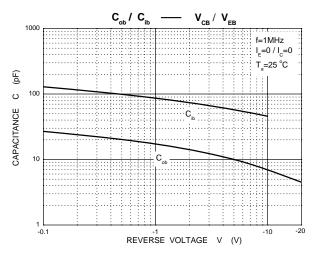


50 75 100

AMBIENT TEMPERATURE T_a (°C)





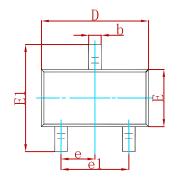


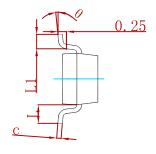


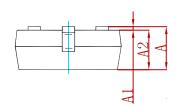
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PACKAGE MECHANICAL DATA

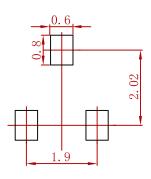






Cumhal	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037	7 TYP	
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

Suggested Pad Layout



- 1.Controlling dimension:in millimeters.2.General tolerance:± 0.05mm.3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
MMBTA94-MS	SOT-23	3000



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